BTA310-800D



3Q Hi-Com Triac
Rev. 1 — 23 April 2012

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

1.3 Applications

- Electronic thermostats (heating and cooling)
- Motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see $Figure 4$; see $Figure 5$	-	-	85	A
Tj	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 106 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	10	Α



Table 1. Quick reference data ...continued

Parameter	Conditions	Min	Тур	Max	Unit
racteristics					
gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } T}$	0.3	-	5	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } T_j}$	0.3	-	5	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ Composition}}$	0.3	-	5	mA
Characteristics					
rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
rate of change of commutating current	$V_D = 400 \text{ V}$; $T_j = 125 \text{ °C}$; $I_{T(RMS)} = 10 \text{ A}$; $dV_{com}/dt = 1 \text{ V/}\mu\text{s}$; gate open circuit	4.5	-	-	A/ms
	gate trigger current Characteristics rate of rise of off-state voltage rate of change of commutating	gate trigger current $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 - G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 - G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_{DM} = 536 \text{ V; } T_j = 125 \text{ °C; }$ $(V_{DM} = 67\% \text{ of } V_{DRM}); \text{ exponential waveform; gate open circuit}$ $V_D = 400 \text{ V; } T_j = 125 \text{ °C; }$ $I_{T(RMS)} = 10 \text{ A; } dV_{com}/dt = 1 \text{ V/}\mu\text{s; }$	gate trigger current $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;} \qquad 0.3$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;} \qquad 0.3$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} \qquad 0.3$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} \qquad 0.3$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ $V_{DM} = 536 \text{ V; } T_j = 125 \text{ °C;} \qquad 20$ $(V_{DM} = 67\% \text{ of } V_{DRM}); \text{ exponential waveform; gate open circuit}}$ $\text{rate of change of commutating current}$ $V_D = 400 \text{ V; } T_j = 125 \text{ °C;} \qquad 4.5$ $I_{T(RMS)} = 10 \text{ A; } dV_{com}/dt = 1 \text{ V/}\mu\text{s;}$	gate trigger current $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+; \\ T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}} \\ V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-; \\ T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}} \\ V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 - G-; \\ T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}} \\ V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 - G-; \\ T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}} \\ \text{Characteristics} \\ \text{rate of rise of off-state voltage} \\ V_{DM} = 536 \text{ V; } T_j = 125 \text{ °C; } \\ (V_{DM} = 67\% \text{ of } V_{DRM}); \text{ exponential waveform; gate open circuit}} \\ \text{rate of change of commutating current} \\ V_D = 400 \text{ V; } T_j = 125 \text{ °C; } \\ I_{T(RMS)} = 10 \text{ A; } \text{dV}_{com}/\text{dt} = 1 \text{ V/}\mu\text{s;}} \\ \text{4.5} \text{-} \\ $	$ \begin{array}{c} \text{ gate trigger current} \\ \text{ gate trigger current} \\ & \begin{array}{c} V_D = 12 \ \text{V}; \ I_T = 0.1 \ \text{A}; \ T2 + \text{G+}; \\ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \ \frac{\text{Figure} \ 7}{\text{Figure} \ 7} \\ \end{array} \\ & \begin{array}{c} V_D = 12 \ \text{V}; \ I_T = 0.1 \ \text{A}; \ T2 + \text{G-}; \\ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \ \frac{\text{Figure} \ 7}{\text{Figure} \ 7} \\ \end{array} \\ & \begin{array}{c} V_D = 12 \ \text{V}; \ I_T = 0.1 \ \text{A}; \ T2 + \text{G-}; \\ V_D = 12 \ \text{V}; \ I_T = 0.1 \ \text{A}; \ T2 - \text{G-}; \\ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \ \frac{\text{Figure} \ 7}{\text{Figure} \ 7} \\ \end{array} \\ & \begin{array}{c} \text{Characteristics} \\ \end{array} \\ & \text{rate of rise of off-state voltage} \\ & \begin{array}{c} V_{DM} = 536 \ \text{V}; \ T_j = 125 \ ^{\circ}\text{C}; \\ (V_{DM} = 67\% \ \text{of} \ V_{DRM}); \ \text{exponential} \\ & \text{waveform; gate open circuit} \\ \end{array} \\ & \text{rate of change of commutating} \\ & \begin{array}{c} V_D = 400 \ \text{V}; \ T_j = 125 \ ^{\circ}\text{C}; \\ I_{T(RMS)} = 10 \ \text{A}; \ \text{d}V_{com}/\text{dt} = 1 \ \text{V}/\mu\text{s}; \\ \end{array} \\ \end{array} $

2. Pinning information

Table 2. Pinning information

I GOIO E.		mormation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		NI
2	T2	main terminal 2	mb	T2—T1
3	G	gate		`G sym051
mb	T2	mounting base; main terminal 2	1 2 3	
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA310-800D	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
repetitive peak off-state voltage		-	800	V
RMS on-state current	full sine wave; $T_{mb} \le 106 ^{\circ}\text{C}$; see Figure 1; see Figure 2; see Figure 3	-	10	Α
non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	85	Α
	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$	-	93	Α
I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	36.1	A ² s
rate of rise of on-state current	$I_T = 20 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
peak gate current		-	2	Α
peak gate power		-	5	W
average gate power	over any 20 ms period	-	0.5	W
storage temperature		-40	150	°C
junction temperature		-	125	°C
	repetitive peak off-state voltage RMS on-state current non-repetitive peak on-state current I ² t for fusing rate of rise of on-state current peak gate current peak gate power average gate power storage temperature	repetitive peak off-state voltage RMS on-state current	repetitive peak off-state voltage RMS on-state current full sine wave; $T_{mb} \le 106 ^{\circ}\text{C}$; see Figure 1; see Figure 2; see Figure 3 non-repetitive peak on-state current full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see Figure 4; see Figure 5 full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - I²t for fusing $t_p = 10 \text{ms}$; sine-wave pulse rate of rise of on-state current $t_T = 20 \text{A}$; $t_G = 0.2 \text{A}$; $t_G = 0.2 \text{A}$ /µs - peak gate current peak gate power average gate power over any 20 ms period - storage temperature - - - - - - - - - - - - -	repetitive peak off-state voltage - 800 RMS on-state current full sine wave; $T_{mb} \le 106 ^{\circ}\text{C}$; see Figure 1; see Figure 2; see Figure 3 non-repetitive peak on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see Figure 4; see Figure 5 full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state current full sine wave; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$ - 93 In the state of rise of on-state c

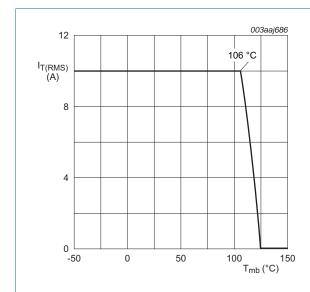


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

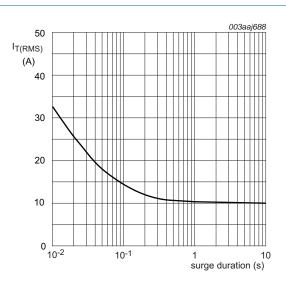


Fig 2. RMS on-state current as a function of surge duration; maximum values

f = 50 Hz; $T_{mb} = 106$ °C

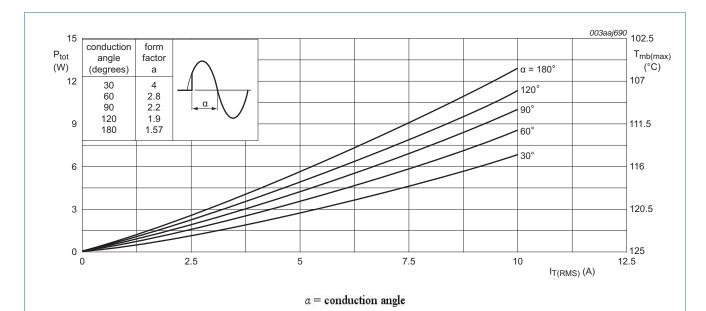


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

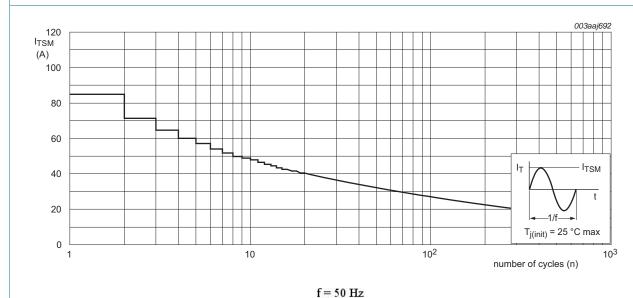
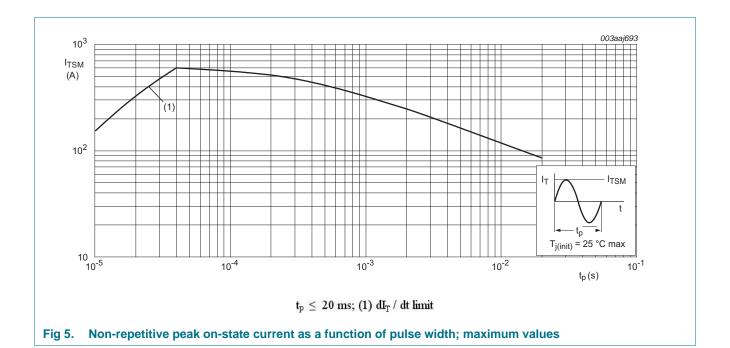


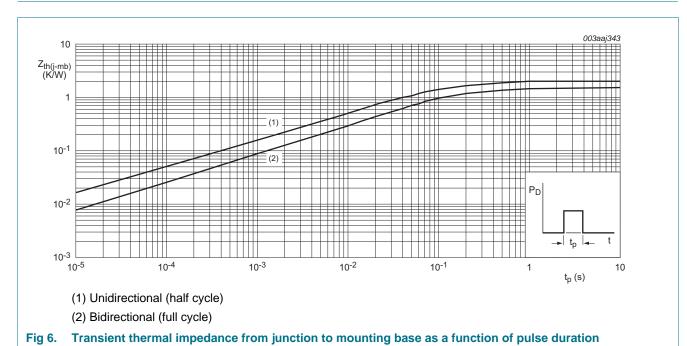
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

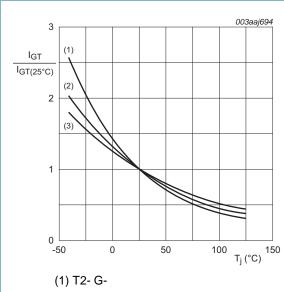
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	full cycle; see Figure 6	-	-	1.5	K/W
	mounting base	half cycle; see Figure 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Characteristics

Table 6. Characteristics

Table 0.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 7	0.3	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-; } T_j = 25 ^{\circ}\text{C;}$ see Figure 7	0.3	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- } G\text{-; } T_j = 25 \text{ °C; } $ see Figure 7	0.3	-	5	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 °C;$ see Figure 8	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-}; T_j = 25 \text{ °C};$ see Figure 8	-	-	15	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	10	mΑ
V _T	on-state voltage	$I_T = 12 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$	-	1.25	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic	Characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; (snubberless condition); gate open circuit$	1	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; \text{ gate open circuit}$	1.5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 10 \text{ A};$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s}; \text{ gate open circuit}$	4.5	-	-	A/ms



- (2) T2+ G+
- (3) T2+ G-

Fig 7. Normalized gate trigger current as a function of junction temperature

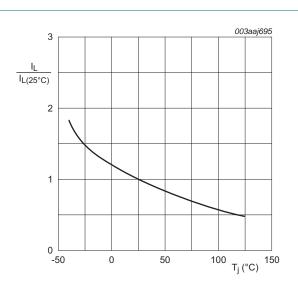


Fig 8. Normalized latching current as a function of junction temperature

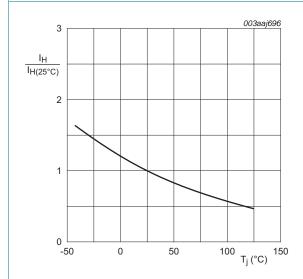
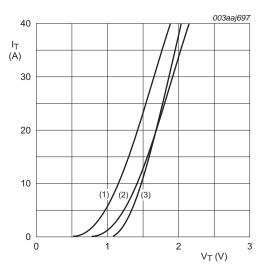


Fig 9. Normalized holding current as a function of junction temperature



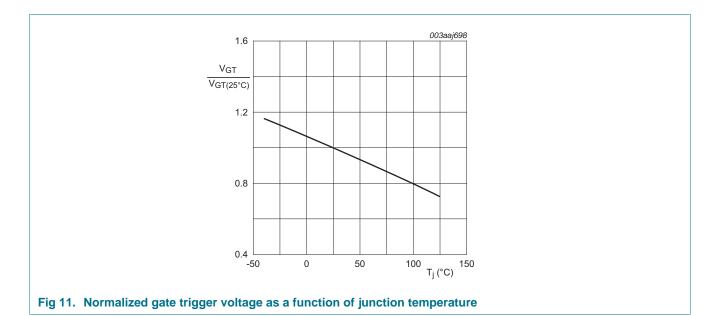
 $V_o = 1.103 \text{ V}; R_s = 0.030 \Omega$

(1) T_i = 125 °C; typical values

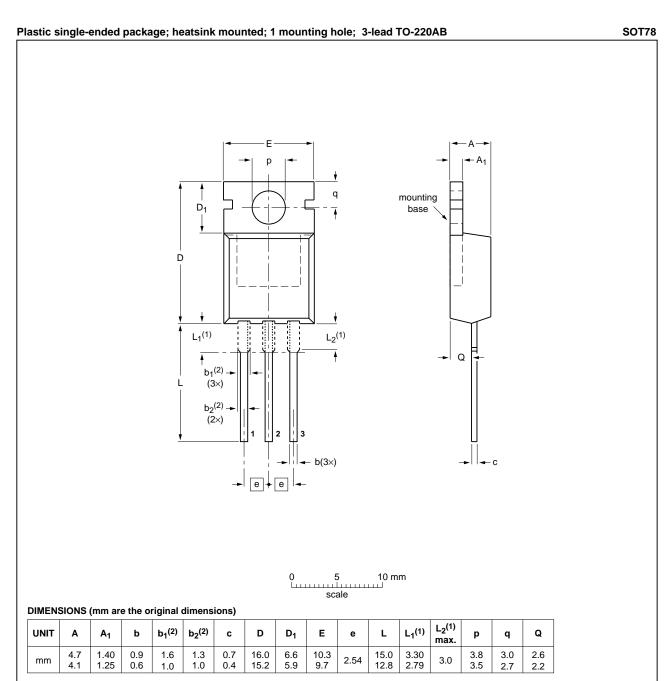
(2) T_j = 125 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig 10. On-state current as a function of on-state voltage



7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN		ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

Fig 12. Package outline SOT78 (TO-220AB)

BTA310-800D

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA310-800D v.1	20120423	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics6
6	Characteristics7
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks
10	Contact information

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